TOSHIBA TLP121

TOSHIBA PHOTOCOUPLER GaAs IRED & PHOTO-TRANSISTOR

TLP121

OFFICE MACHINE

PROGRAMMABLE CONTROLLERS

AC/DC-INPUT MODULE

TELECOMMUNICATION

The TOSHIBA MINI FLAT COUPLER TLP121 is a small outline coupler, suitable for surface mount assembly.

TLP121 consists of a photo transistor, optically coupled to a gallium arsenide infrared emitting diode.

• Collector-Emitter Voltage: 80V (Min.)

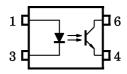
• Current Transfer Ratio : 50% (Min.)

Rank GB : 100% (Min.)

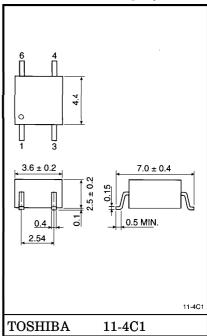
• Isolation Voltage : 3750Vrms (Min.)

• UL Recognized : UL 1577, File No. E67349

PIN CONFIGURATIONS (TOP VIEW)



1 : ANODE 3 : CATHODE 4 : EMITTER 6 : COLLECTOR Unit in mm



Weight: 0.09g

CURRENT TRANSFER RATIO

| TYPE | CLASSIFICATION | CURRENT 'RATI | O (%) | MARKING OF CLASSIFICATION | | |
|--------|----------------|--|-------|---|--|--|
| | *1 | $I_{\mathrm{F}}=5\mathrm{mA},\ V_{\mathrm{CE}}=5\mathrm{V},\ \mathrm{Ta}=25^{\circ}\mathrm{C}$ | | | | |
| | | MIN. | MAX. | | | |
| | (None) | 50 | 600 | BLANK, Y, Y [■] , G, G [■] , B, B [■] , GB | | |
| | Rank Y | 50 | 150 | Y, Y ■ | | |
| TLP121 | Rank GR | 100 | 300 | G, G [■] | | |
| | _ | 200 | 600 | В, В■ | | |
| | Rank GB | 100 | 600 | G, G [■] , B, B [■] , GB | | |

^{*1 :} Ex, Rank GB : TLP121 (GB)

Note: Application type name for certification test, please use standard product type name, i,

e.

TLP121 (GB) : TLP121

MAXIMUM RATINGS (Ta = 25°C)

| | CHARACTERISTIC | SYMBOL | RATING | UNIT |
|---|---|--|--|-------|
| | Forward Current | ${ m I_F}$ | 50 | mA |
| | Forward Current Derating | $\Delta I_{\mathbf{F}}/^{\circ}\mathbf{C}$ | -0.7 (Ta≥53°C) | mA/°C |
| LED | Pulse Forward Current | $I_{	extbf{FP}}$ | $1(100\mu\mathrm{s}$ pulse, $100\mathrm{pps})$ | A |
| | Reverse Voltage | $v_{ m R}$ | 5 | V |
| | Junction Temperature | $\mathrm{T_{j}}$ | 125 | °C |
| | Collector-Emitter Voltage | v_{CEO} | 80 | V |
|).R | Emitter-Collector Voltage | v_{ECO} | 7 | V |
| DETECTOR | Collector Current | $I_{\mathbf{C}}$ | 50 | mA |
| ľE(| Collector Power Dissipation | $P_{\mathbf{C}}$ | 150 | mW |
| DE, | Collector Power Dissipation Derating (Ta≥25°C) | ΔP _C /°C | -1.5 | mW/°C |
| | Junction Temperature | T_{j} | 125 | °C |
| Sto | rage Temperature Range | $\mathrm{T_{stg}}$ | -55~125 | °C |
| Оре | erating Temperature Range | ${ m T_{opr}}$ | -55~100 | °C |
| Lead Soldering Temperature | | $T_{ m sol}$ | 260 (10s) | °C |
| Total Package Power Dissipation | | P_{T} | 200 | mW |
| Total Package Power Dissipation Derating (Ta≥25°C) | | $\Delta \mathrm{P_T/^\circ C}$ | -2.0 | mW/°C |
| Isolation Voltage (Note 1) | | $BV_{\mathbf{S}}$ | 3750 (AC, 1min., R.H.≤60%) | Vrms |

(Note 1) Device considered a two terminal device: Pins 1, 3 shorted together and pins 4, 6 shorted together

RECOMMENDED OPERATING CONDITIONS

| CHARACTERISTIC | SYMBOL | MIN. | TYP. | MAX. | UNIT |
|-----------------------|------------------|------|------|------|----------------------|
| Supply Voltage | v_{CC} | | 5 | 48 | V |
| Forward Current | $I_{\mathbf{F}}$ | 1 | 16 | 20 | mA |
| Collector Current | $I_{\mathbf{C}}$ | | 1 | 10 | mA |
| Operating Temperature | $T_{ m opr}$ | -25 | _ | 85 | $^{\circ}\mathrm{C}$ |

INDIVIDUAL ELECTRICAL CHARACTERISTICS (Ta = 25°C)

| | CHARACTERISTIC | SYMBOL | TEST CONDITION | MIN. | TYP. | MAX. | UNIT |
|----------|--|---------------------------|---------------------------------|------|------|------|---------|
| | Forward Voltage | $ m V_{f F}$ | $I_{ m F} = 10 { m mA}$ | 1.0 | 1.15 | 1.3 | V |
| LED | Reverse Current | $I_{\mathbf{R}}$ | $V_R=5V$ | _ | _ | 10 | μ A |
| | Capacitance | C_{T} | V=0, f=1MHz | _ | 30 | _ | pF |
| | Collector-Emitter Breakdown Voltage | V _{(BR)CEO} | $I_{ m C}\!=\!0.5{ m mA}$ | 80 | _ | _ | V |
| DETECTOR | Emitter-Collector Breakdown Voltage | V _{(BR)ECO} | $I_{\rm E}\!=\!0.1{ m mA}$ | 7 | _ | _ | V |
| TE | Collector Dark Current | Iono | $V_{\rm CE} = 48V$ | | 10 | 100 | nA |
| DE | Collector Dark Current | ICEO | $V_{CE}=48V$, $Ta=85^{\circ}C$ | _ | 2 | 50 | μ A |
| | Capacitance (Collector to Emitter) | c_{CE} | V=0, f=1MHz | _ | 10 | _ | pF |

COUPLED ELECTRICAL CHARACTERISTICS (Ta = 25°C)

| CHARACTERISTIC | SYMBOL | TEST CONDITION | MIN. | TYP. | MAX. | UNIT |
|--------------------------------------|----------------------|---|------|----------|------|---------|
| Current Transfer Ratio | $I_{ m C}/I_{ m F}$ | $I_{F}=5mA, V_{CE}=5V$ | 50 | _ | 600 | % |
| | -C / -F | Rank GB | 100 | — | 600 | " |
| Saturated CTR | IC/IF(sat) | I _F =1mA, V _{CE} =0.4V Rank GB | _ | 60 | | - % |
| Saturated CIR | | | 30 | _ | _ | 70 |
| | V _{CE(sat)} | I_{C} =2.4mA, I_{F} =8mA | _ | _ | 0.4 | |
| Collector-Emitter Saturation Voltage | | I _C =0.2mA, I _F =1mA Rank GB | _ | 0.2 | _ |] v |
| | | | _ | _ | 0.4 | |
| Off-State Collector Current | $I_{C(off)}$ | $V_{F} = 0.7V, V_{CE} = 48V$ | _ | 1 | 10 | μ A |

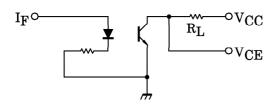
ISOLATION CHARACTERISTICS (Ta = 25°C)

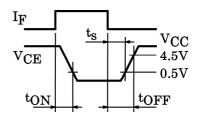
| CHARACTERISTIC | SYMBOL | TEST CONDITION | MIN. | TYP. | MAX. | UNIT |
|-------------------------------|----------------------------|--------------------------------|--------------------|-----------|------|------|
| Capacitance (Input to Output) | c_{S} | $V_S=0$, f=1MHz | _ | 0.8 | _ | рF |
| Isolation Resistance | $R_{\mathbf{S}}$ | V _S =500V, R.H.≦60% | 5×10^{10} | 10^{14} | _ | Ω |
| | BV_{S} | AC, 1 minute | 3750 | I | _ | |
| Isolation Voltage | | AC, 1 second, in oil | _ | 10000 | _ | Vrms |
| | | DC, 1 minute, in oil | | 10000 | _ | Vdc |

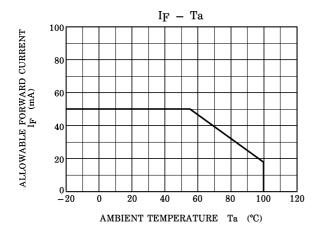
SWITCHING CHARACTERISTICS (Ta = 25°C)

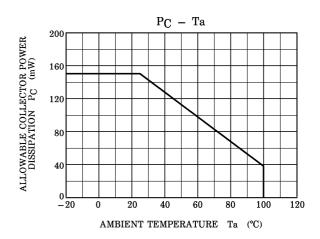
| CHARACTERISTIC | SYMBOL | TEST CONDITION | MIN. | TYP. | MAX. | UNIT |
|----------------|------------------|--|------|------|------|---------|
| Rise Time | $t_{\mathbf{r}}$ | $V_{\rm CC}$ =10V, $I_{\rm C}$ =2mA $R_{\rm L}$ =100 Ω | _ | 2 | _ | |
| Fall Time | t_f | | _ | 3 | _ |] |
| Turn-on Time | ton | | _ | 3 | _ | μ s |
| Turn-off Time | $t_{ m off}$ | | _ | 3 | _ | |
| Turn-on Time | ton | R_L =1.9k Ω (Fig.1) V_{CC} =5V, I_F =16mA | _ | 2 | _ | |
| Storage Time | ${ m t_S}$ | | _ | 25 | _ | μ s |
| Turn-off Time | tOFF | | _ | 40 | _ | |

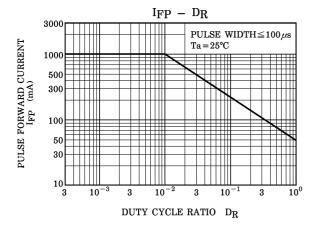
Fig.1 SWITCHING TIME TEST CIRCUIT

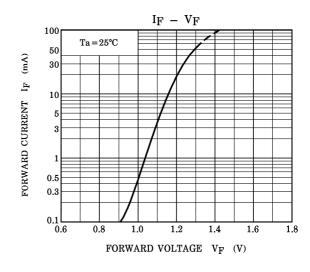


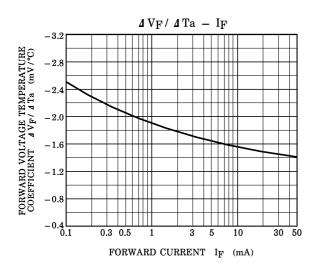


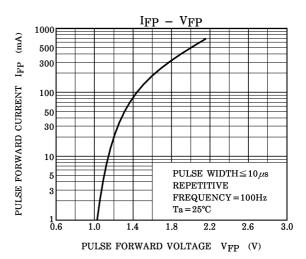


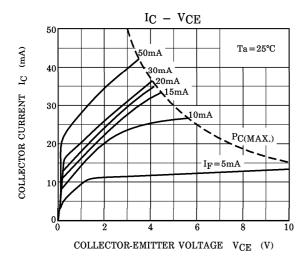


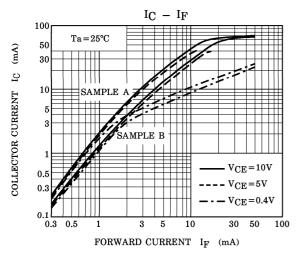


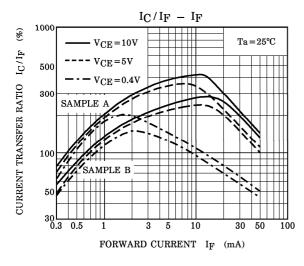


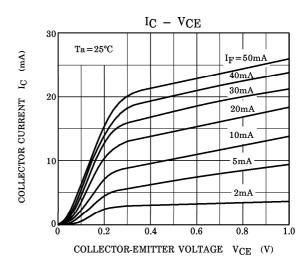


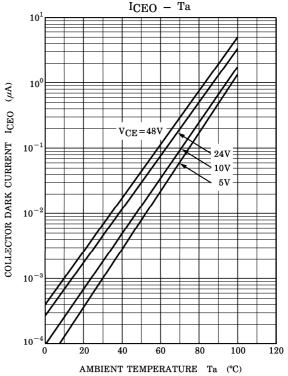


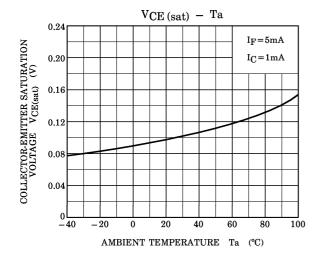


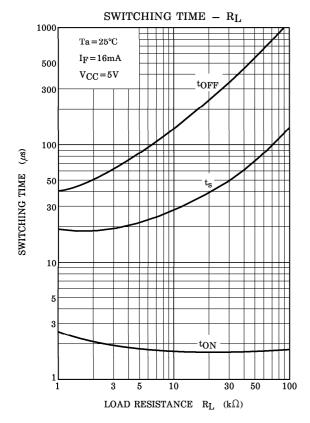


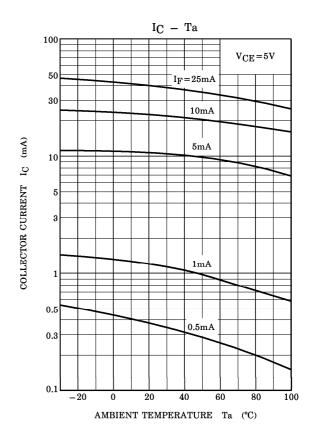












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